



P-Channel Enhancement-Mode MOSFET Transistors

PRODUCT SUMMARY

Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
VP0300B	-30	2.5 @ $V_{GS} = -12$ V	-2 to -4.5	-1.25
VP0300L		2.5 @ $V_{GS} = -12$ V	-2 to -4.5	-0.32
VP0300LS		2.5 @ $V_{GS} = -12$ V	-2 to -4.5	-0.5
VQ2001J		2 @ $V_{GS} = -12$ V	-2 to -4.5	-0.6
VQ2001P		2 @ $V_{GS} = -12$ V	-2 to -4.5	-0.6

FEATURES

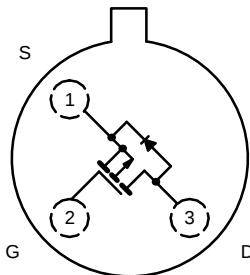
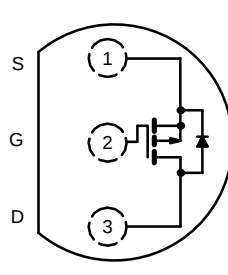
- High-Side Switching
- Low On-Resistance: 1.5 Ω
- Moderate Threshold: -3.1 V
- Fast Switching Speed: 17 ns
- Low Input Capacitance: 60 pF

BENEFITS

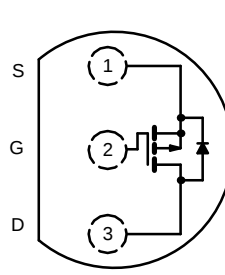
- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Switching
- Easily Driven Without Buffer

APPLICATIONS

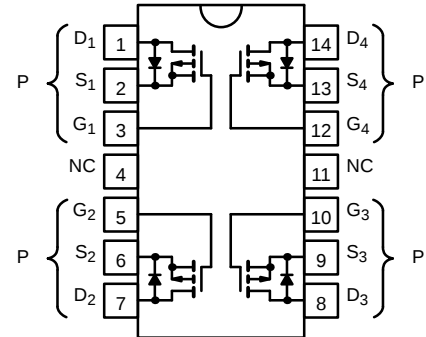
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply, Converter Circuits
- Motor Control

TO-205AD (TO-39)
(Case Drain)Top View
VP0300BTO-226AA
(TO-92)Top View
VP0300L

TO-92S

Top View
VP0300LS

Dual-In-Line

Top View
Plastic: VQ2001J
Sidebrazed: VQ2001PABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	VP0300B	VP0300L	VP0300LS	VQ2001J/P		Unit
					Single	Total Quad	
Drain-Source Voltage	V_{DS}	-30	-30	-30	-30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	± 20	± 20	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	-1.25 ^b	-0.32	-0.5	-0.6	-0.6	A
		-0.79 ^b	-0.2	-0.32	-0.37	-0.37	
Pulsed Drain Current ^a	I_{DM}	-3	-2.4	-3	-2	-2	
Power Dissipation	P_D	6.25 ^b	0.8	0.9	1.3	2	W
		2.5 ^b	0.32	0.4	0.52	0.8	
Maximum Junction-to-Ambient	R_{thJA}	20 ^b	156	139	96	62.5	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150					$^\circ\text{C}$

Notes

a. Pulse width limited by maximum junction temperature.

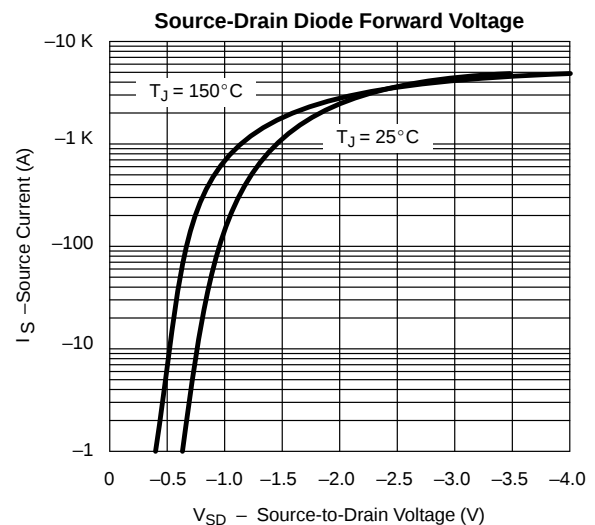
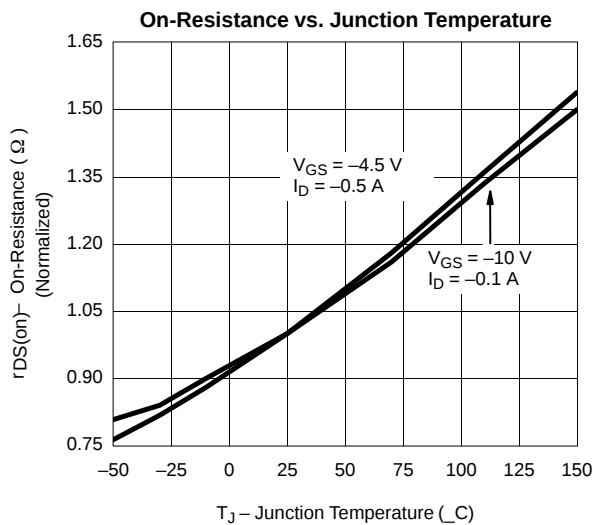
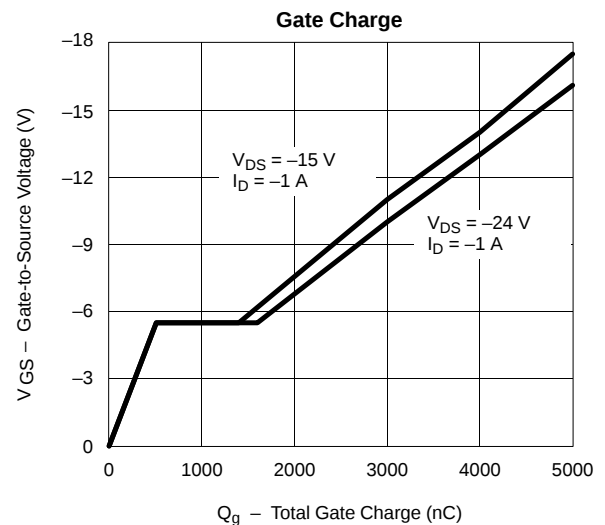
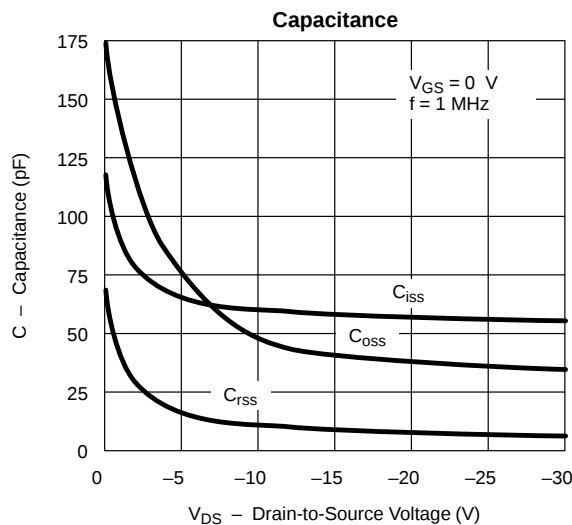
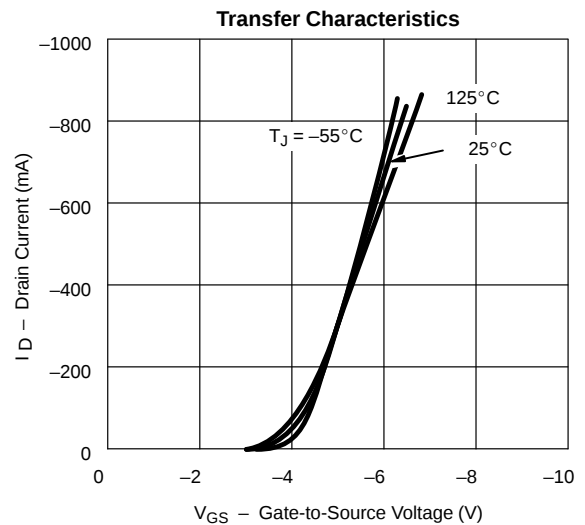
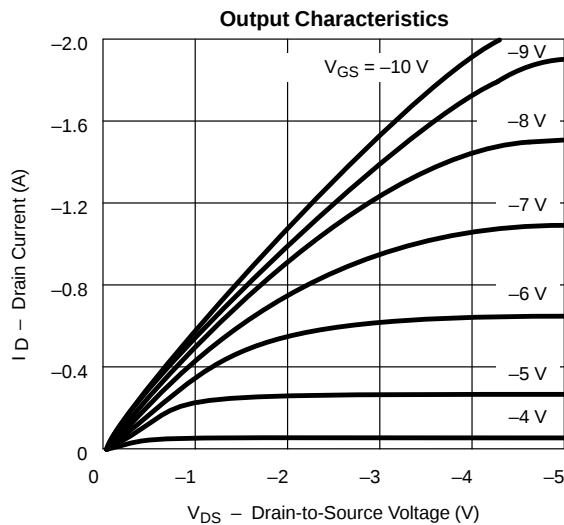
b. Power dissipation and continuous drain current at $T_C = 25^\circ\text{C}$; $R_{thJC} = 20^\circ\text{C/W}$.

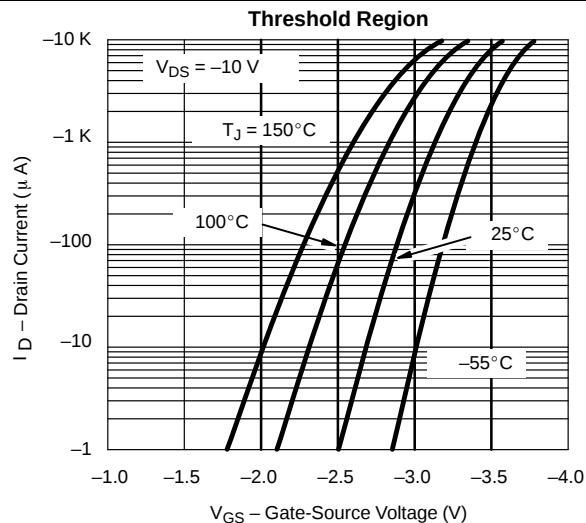
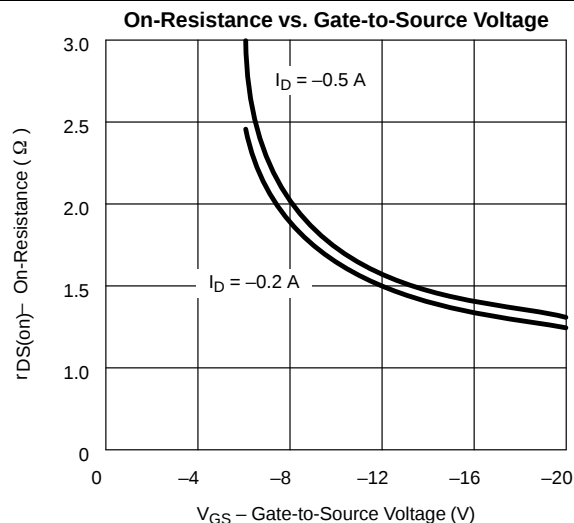
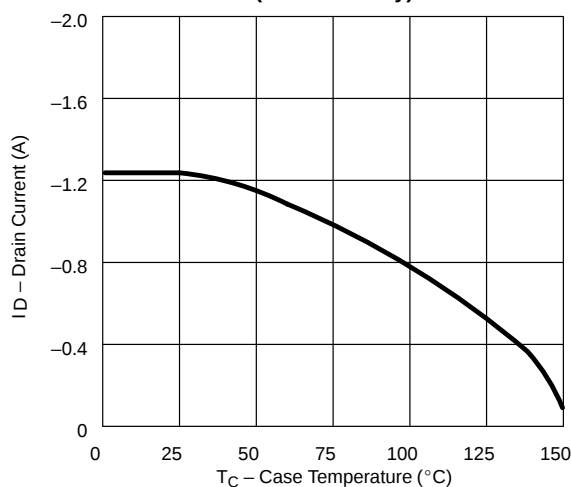
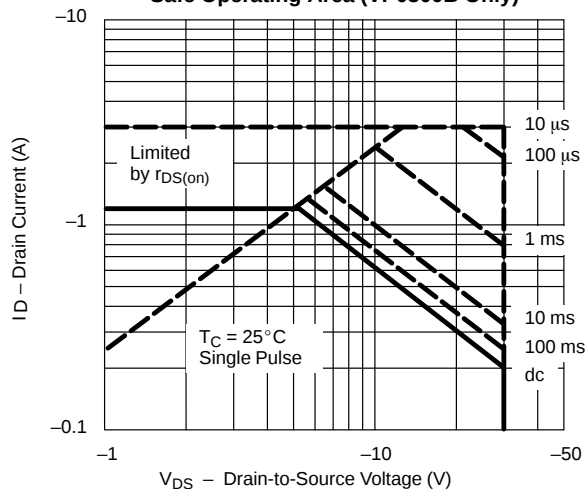
Applications information may also be obtained via FaxBack, request document #70611.

SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Typ ^a	Limits				Unit
				VP0300B/L/LS		VQ2001J/P		
				Min	Max	Min	Max	
Static								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = −10 μA	−55	−30		−30		V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = −1 mA	−3.1	−2	−4.5	−2	−4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 16 V					± 100	nA
		T _J = 125°C V _{DS} = 0					± 500	



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**THERMAL RATINGS****Maximum Drain Current vs. Case Temperature (VP0300B Only)****Safe Operating Area (VP0300B Only)****Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-226AA, VP0300L Only)**